IN THE CLAIMS:

1. (Original) A semiconductor light emitting device comprising:

a base substrate;

a multilayer epitaxial structure that includes a first conductive layer, a second conductive layer and a light emitting layer that is formed between the first conductive layer and the second conductive layer, the multilayer epitaxial structure being formed on the base substrate in such a manner that the first conductive layer is positioned closer to the base substrate than the second conductive layer is; and

a phosphor film that covers a main surface of the multilayer epitaxial structure which faces away from the base substrate, and every side surface of the multilayer epitaxial structure from a layer including the main surface to include at least the light emitting layer.

2. (Original) The semiconductor light emitting device of Claim 1, wherein

the multilayer epitaxial structure is epitaxially grown on the base substrate.

3. (Original) The semiconductor light emitting device of Claim 2, wherein

the multilayer epitaxial structure further includes a reflective layer which is formed between the base substrate and the first conductive layer.

4. (Original) The semiconductor light emitting device of Claim 3, wherein

the reflective layer is made of an AlGaN semiconductor.

5. (Original) The semiconductor light emitting device of Claim 2, further comprising:

a first electrode that is formed on the first conductive layer;

a second electrode that is formed on the second conductive layer;

a first power supply terminal and a second power supply terminal that are formed on a main surface of the base substrate which faces away from the multilayer epitaxial structure;

a first conductive member including a first through hole that is provided in the base substrate, and electrically connecting the first electrode and the first power supply terminal; and

a second conductive member including a second through hole that is provided in the base substrate, and electrically connecting the second electrode and the second power supply terminal.

6. (Original) The semiconductor light emitting device of Claim 5, wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure, and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

7. (Original) The semiconductor light emitting device of Claim 2,

the base substrate is made of one of SiC, AlN, GaN, BN, and Si.

8. (Original) The semiconductor light emitting device of Claim 2, wherein

the main surface of the multilayer epitaxial structure which faces away from the base substrate is uneven so as to improve light extraction efficiency.

9. (Original) The semiconductor light emitting device of Claim 2, wherein light emitted from the light emitting layer has a wavelength component within a range of 380 nm to 780 nm.

10. (Original) The semiconductor light emitting device of Claim 1, wherein the multilayer epitaxial structure is first epitaxially grown on a single-crystal substrate, and then transferred to the base substrate.

11. (Original) The semiconductor light emitting device of Claim 10, further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

12. (Original) The semiconductor light emitting device of Claim 10, wherein the first conductive layer is a p-type semiconductor layer, and the second conductive layer is an n-type semiconductor layer.

13. (Original) The semiconductor light emitting device of Claim 12, wherein a main surface of the n-type semiconductor layer which faces away from the light emitting layer is uneven so as to improve light extraction efficiency.

14. (Original) The semiconductor light emitting device of Claim 1, wherein the multilayer epitaxial structure is shaped as a cylinder having a substantially circular or N-sided polygonal cross-section, where N is an integer equal to or larger than five.

15. (Original) The semiconductor light emitting device of Claim 14, wherein the phosphor film is applied at a substantially same thickness.

16. (Original) The semiconductor light emitting device of Claim 14, wherein the main surface of the base substrate which faces the multilayer epitaxial structure is rectangular.

17. (Original) The semiconductor light emitting device of Claim 14, wherein the multilayer epitaxial structure further includes a light reflective layer which is formed between the first conductive layer and the base substrate.

18. (Original) The semiconductor light emitting device of Claim 14, wherein the multilayer epitaxial structure is epitaxially grown on the base substrate.

19. (Original) The semiconductor light emitting device of Claim 14, wherein the multilayer epitaxial structure is divided into a plurality of portions by a division groove that reaches the base substrate, the plurality of portions being a plurality of independent light emitting elements.

20. (Original) The semiconductor light emitting device of Claim 19, wherein in each of the plurality of independent light emitting elements,
a first electrode is formed on a part of a main surface of the first conductive layer, the part being created by partially removing the second conductive layer and the light emitting layer, and a second electrode is formed on a main surface of the second conductive layer, and
the plurality of independent light emitting elements are connected with each other

in series in such a manner that a first electrode of one independent light emitting element is connected to a second electrode of another independent light emitting element using a wiring formed by a thin metal film.

21. (Original) The semiconductor light emitting device of Claim 20, wherein the light emitting layer included in each independent light emitting element has a substantially same area.

22.-28 (Cancelled)

29. (New) The semiconductor light emitting device of Claim 1 wherein the phosphor film is formed of $(Sr, Ba)_2 Sio_4:Eu^{2+}$.

30. (New) The semiconductor light emitting device of Claim 29 wherein a thickness of the phosphor film is approximately 50 μm.

31. (New) The semiconductor light emitting device of Claim 1 wherein the epitaxial structure has an uneven p-electrode surface as a first conductive layer.

32. (New) The semiconductor light emitting device of Claim 31 wherein a plurality of depressions is formed on a surface of the p-electrode surface to improve light extraction efficiency.

33. (New) The semiconductor light emitting device of Claim 31 wherein a Ni/An thin film and an ITO transparent electrode form the p-electrode.

34. (New) The semiconductor light emitting device of Claim 1 includes a hole in the base substrate.